

High Resolution C1s with Increasing Dose

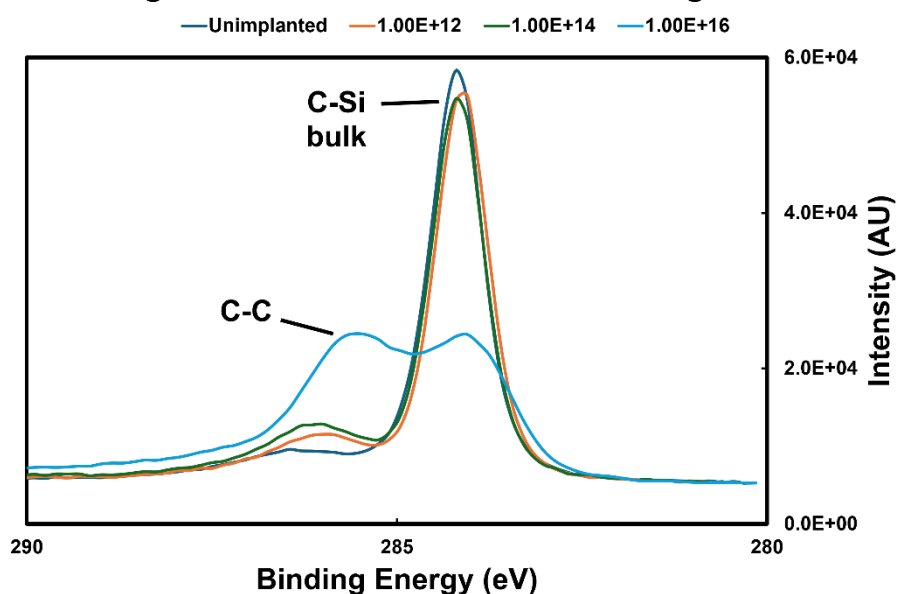


Fig. 1. High resolution XPS spectra of the C1s peak in 4H-SiC with increasing He dose.

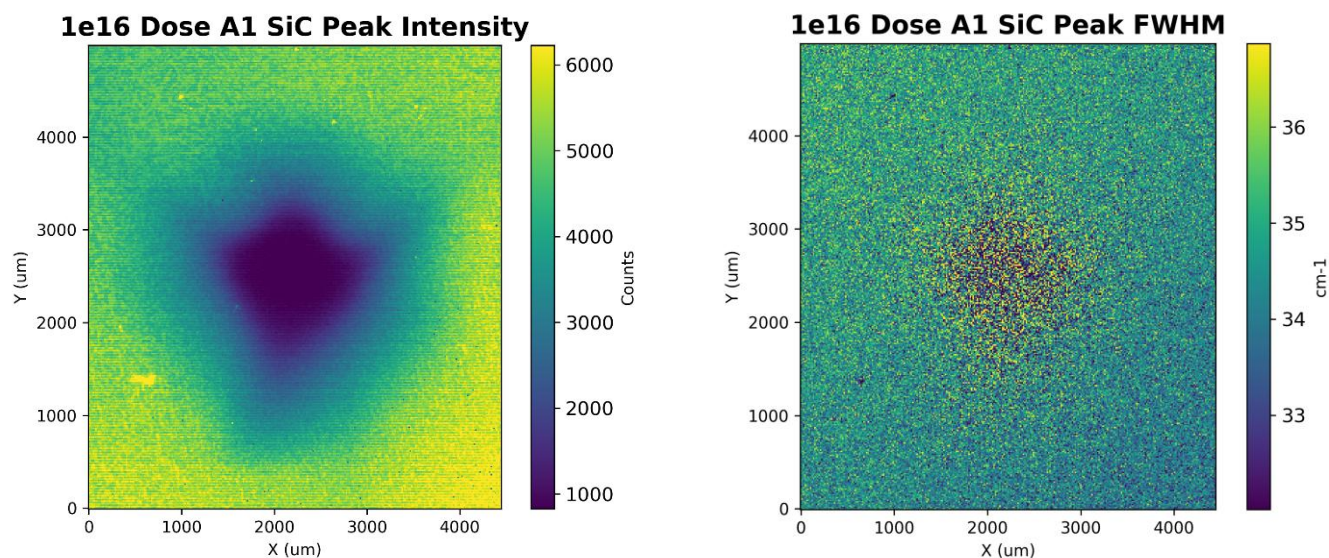


Fig. 2. Raman (left) peak intensity and (right) FWHM of the 980 cm⁻¹ peak attributed to the LO mode found in SiC. The implanted regions shows a reduced intensity and broadening of the FWHM.

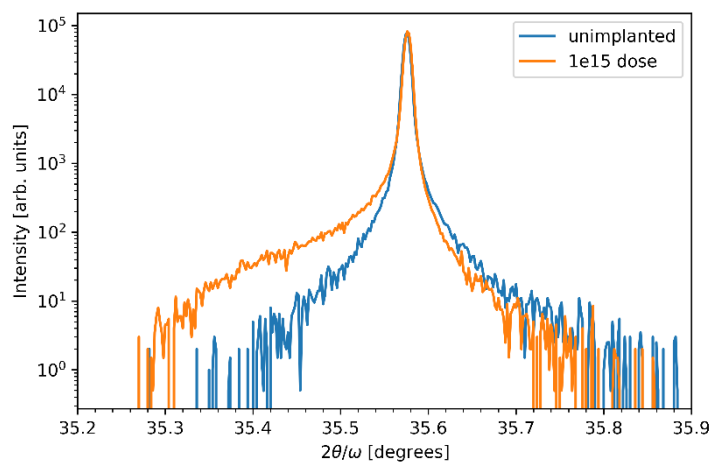


Fig. 3. 2θ/ω scan using HRXRD. Peak broadening is observed for the 1e15 cm⁻² He dose ion implantation compared to the unimplanted region.